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Kind regards,

Team Nexperia

PDTC144V series

NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 10 k Ω

Rev. 04 — 16 November 2009

Product data sheet

1. Product profile

1.1 General description

NPN resistor-equipped transistors.

Table 1. Product overview

Type number	Package	Package		
	NXP	JEITA		
PDTC144VE	SOT416	SC-75	PDTA144VE	
PDTC144VK	SOT346	SC-59A	PDTA144VK	
PDTC144VM	SOT883	SC-101	PDTA144VM	
PDTC144VS[1]	SOT54 (TO-92)	SC-43A	PDTA144VS	
PDTC144VT	SOT23	-	PDTA144VT	
PDTC144VU	SOT323	SC-70	PDTA144VU	

^[1] Also available in SOT54A and SOT54 variant packages (see Section 2).

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- General-purpose switching and amplification
- Inverter and interface circuits

Circuit drivers

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.17	0.21	0.26	



2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
SOT54			
1	input (base)		
2	output (collector)		2
3	GND (emitter)	001aab347	1 R1 R2 R2 3

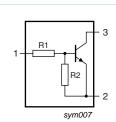
SOT54A			
1	input (base)		
2	output (collector)		2
3	GND (emitter)	001aab348	1 R1 R2 3

SOT54 variant



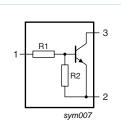
SOT23, SOT323, SOT346, SOT416

1	input (base)	
2	GND (emitter)	[3]
3	output (collector)	1.
		[1] [2]
		006aaa144



SOT883

1	input (base)
2	GND (emitter)
3	output (collector)



2 of 11

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PDTC144VE	SC-75	plastic surface mounted package; 3 leads	SOT416
PDTC144VK	SC-59A	plastic surface mounted package; 3 leads	SOT346
PDTC144VM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883
PDTC144VS[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54
PDTC144VT	-	plastic surface mounted package; 3 leads	SOT23
PDTC144VU	SC-70	plastic surface mounted package; 3 leads	SOT323

^[1] Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PDTC144VE	18
PDTC144VK	29
PDTC144VM	G6
PDTC144VS	TC144V
PDTC144VT	*AA
PDTC144VU	*18

^{[1] * = -:} made in Hong Kong

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	15	V
VI	input voltage				
	positive		-	+40	V
	negative		-	-15	V
Io	output current (DC)		-	100	mA
I _{CM}	peak collector current		-	100	mA
P _{tot}	total power dissipation				
	SOT416	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	150	mW
	SOT346	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	250	mW
	SOT883	$T_{amb} \le 25 ^{\circ}C$	[2][3]	250	mW
	SOT54	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	500	mW
	SOT23	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	250	mW
	SOT323	$T_{amb} \le 25 ^{\circ}C$	[1] -	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C

^[1] Refer to standard mounting conditions.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT416		<u>[1]</u> _	-	833	K/W
	SOT346		<u>[1]</u> _	-	500	K/W
	SOT883		[2][3]	-	500	K/W
	SOT54		<u>[1]</u> _	-	250	K/W
	SOT23		<u>[1]</u> _	-	500	K/W
	SOT323		<u>[1]</u> _	-	625	K/W

^[1] Refer to standard mounting conditions.

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^[2] Reflow soldering is the only recommended soldering method.

^[3] Refer to SOT883 standard mounting conditions; FR4 printed-circuit board with 60 μm copper strip line.

^[2] Reflow soldering is the only recommended soldering method.

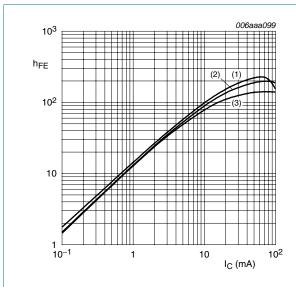
^[3] Refer to SOT883 standard mounting conditions; FR4 printed-circuit board with 60 μm copper strip line.

7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
	cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	50	μА
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$	-	-	150	μА
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	40	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	3.1	1	V
V _{I(on)}	on-state input voltage	$V_{CE} = 300 \text{ mV}; I_{C} = 2 \text{ mA}$	6	3.8	-	V
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.17	0.21	0.26	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2	pF



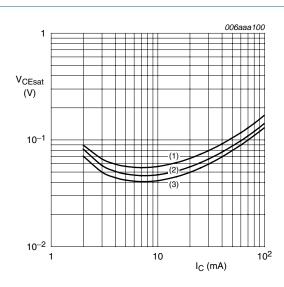
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 1. DC current gain as a function of collector current; typical values



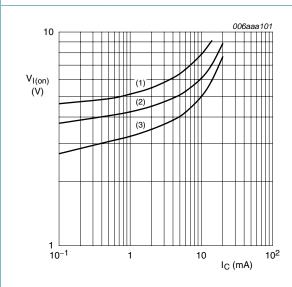
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values



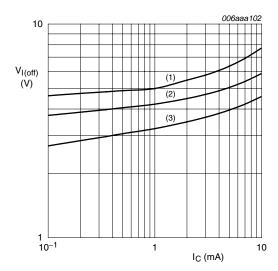


(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

On-state input voltage as a function of Fig 3. collector current; typical values



$$V_{CE} = 5 V$$

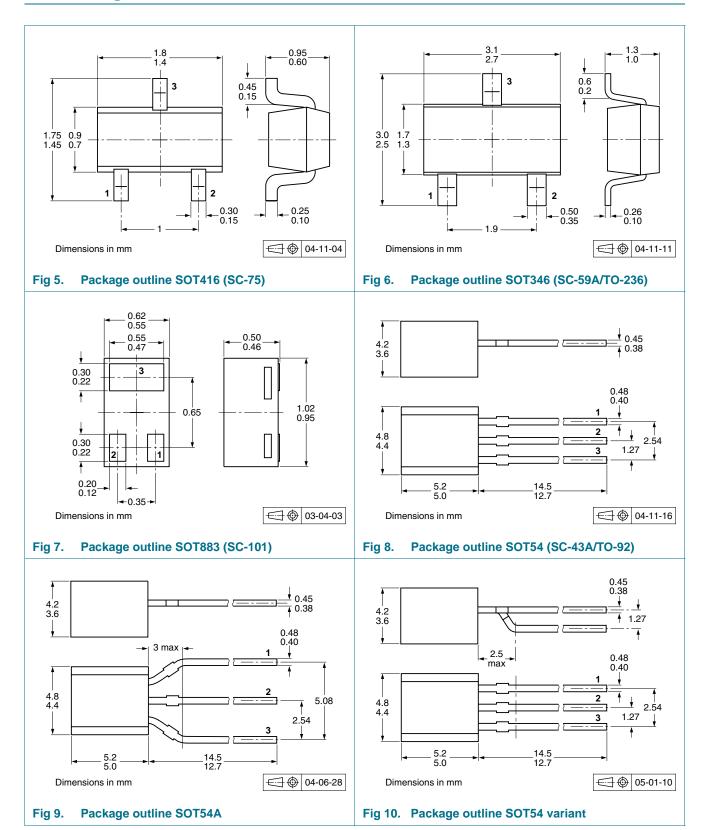
(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

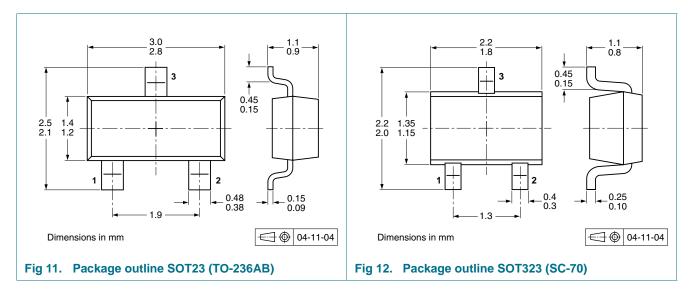
(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 4. Off-state input voltage as a function of collector current; typical values

8. Package outline



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Packing information

Table 9. **Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing q	uantity	
			3000	5000	10000
PDTC144VE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTC144VK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTC144VM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315
PDTC144VS	SOT54	bulk, straight leads	-	-412	-
	SOT54A	tape and reel, wide pitch	-	-	-116
		tape ammopack, wide pitch	-	-	-126
	SOT54 variant	bulk, delta pinning	-	-112	-
PDTC144VT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235
PDTC144VU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135

^[1] For further information and the availability of packing methods, see Section 12.

PDTC144V series

NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 10 k Ω

10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
PDTC144V_SER_4	20091116	Product data sheet	-	PDTC144V_SER_3	
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. 				
DDT04404 0ED 0					
PDTC144V_SER_3	20050215	Product data sheet	-	PDTC144VT_2	
PDTC144V_SER_3 PDTC144VT_2	20050215 20040511	Product data sheet Objective data sheet	-	PDTC144VT_2 PDTC144VT_1	

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PDTC144V series

NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 10 k Ω

13. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications
1.4	Quick reference data
2	Pinning information
3	Ordering information
4	Marking
5	Limiting values
6	Thermal characteristics
7	Characteristics
8	Package outline
9	Packing information
10	Revision history
11	Legal information
11.1	Data sheet status
11.2	Definitions
11.3	Disclaimers
11.4	Trademarks10
12	Contact information
13	Contents

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